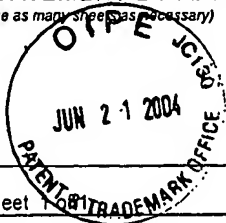


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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	10/786,726
Filing Date	February 25, 2004
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Unknown

Sheet 1

Attorney Docket No: 303.680US3

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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 1 of 3

Attorney Docket No: 303.680US3

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Application Number	Unknown
Filing Date	Even Date Herewith
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Unknown

Sheet 2 of 3

Attorney Docket No: 303.680US3

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Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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Kane. Koman

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7/20/94

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Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)	Complete if Known	
	Application Number	Unknown
	Filing Date	Even Date Herewith
	First Named Inventor	Forbes, Leonard
	Group Art Unit	Unknown
	Examiner Name	Unknown
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